

Tao Han

List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	A high performance trench gate tunneling field effect transistor based on quasi-broken gap energy band alignment heterojunction. Nanotechnology, 2022, 33, 225205.	2.6	6
2	Investigation of Negative Bias Temperature Instability Effect in Nano PDSOI PMOSFET. Micromachines, 2022, 13, 808.	2.9	0
3	MANet: Multi-Scale Aware-Relation Network for Semantic Segmentation in Aerial Scenes. IEEE Transactions on Geoscience and Remote Sensing, 2022, 60, 1-15.	6.3	14
4	Adjusting transmissivity based on graphemeâ€h-BNâ€graphene heterostructure as a tunable phononâ€plasmon coupling system in mid-infrared band. Journal of Materials Science, 2021, 56, 3210-3219.	3.7	3
5	Synthesis and Spectral Characteristics Investigation of the 2D-2D vdWs Heterostructure Materials. International Journal of Molecular Sciences, 2021, 22, 1246.	4.1	2
6	Investigation of charge trapping mechanism in MoS ₂ field effect transistor by incorporating Al into host La ₂ O ₃ as gate dielectric. Nanotechnology, 2021, 32, 305201.	2.6	5
7	Low-Power OR Logic Ferroelectric In-Situ Transistor Based on a CuInP2S6/MoS2 Van Der Waals Heterojunction. Nanomaterials, 2021, 11, 1971.	4.1	5
8	Construction and electrical performance improvement of MoS ₂ FET with graphene/metal contact. Optical Materials Express, 2021, 11, 3099.	3.0	2
9	Preparation and Research of Monolayer WS2 FETs Encapsulated by h-BN Material. Micromachines, 2021, 12, 1006.	2.9	5
10	First-Principles Study on the Effect of Strain on Single-Layer Molybdenum Disulfide. Nanomaterials, 2021, 11, 3127.	4.1	9
11	Improvement of Electrical Performance in Heterostructure Junctionless TFET Based on Dual Material Gate. Applied Sciences (Switzerland), 2020, 10, 126.	2.5	18
12	Comprehensive Performance Quasi-Non-Volatile Memory Compatible with Large-Scale Preparation by Chemical Vapor Deposition. Nanomaterials, 2020, 10, 1471.	4.1	4
13	Fabrication and Characterization of MoS2/h-BN and WS2/h-BN Heterostructures. Micromachines, 2020, 11, 1114.	2.9	11
14	Graphene Electro-Optical Switch Modulator by Adjusting Propagation Length Based on Hybrid Plasmonic Waveguide in Infrared Band. Sensors, 2020, 20, 2864.	3.8	8
15	TCAD simulation of a double L-shaped gate tunnel fieldâ€effect transistor with a covered sourceâ€channel. Micro and Nano Letters, 2020, 15, 272-276.	1.3	11
16	Electrical performance of InAs/GaAs _{0.1} Sb _{0.9} heterostructure junctionless TFET with dual-material gate and Gaussian-doped source. Semiconductor Science and Technology, 2020, 35, 095004.	2.0	13
17	Filtering Characteristics of Phonon Polaritons Waves Based on Dielectric-h-BN-Dielectric Structure in Mid-Infrared Band. Nanomaterials, 2020, 10, 878.	4.1	1
18	The Large-Scale Preparation and Optical Properties of MoS2/WS2 Vertical Hetero-Junction. Molecules, 2020, 25, 1857.	3.8	7

#	ARTICLE	IF	CITATIONS
19	TCAD Simulation of the Doping-Less TFET with Ge/SiGe/Si Hetero-Junction and Hetero-Gate Dielectric for the Enhancement of Device Performance. <i>Coatings</i> , 2020, 10, 278.	2.6	4
20	Research on the Preparation and Spectral Characteristics of Graphene/TMDs Hetero-structures. <i>Nanoscale Research Letters</i> , 2020, 15, 219.	5.7	8
21	A Novel Dopingless Fin-Shaped SiGe Channel TFET with Improved Performance. <i>Nanoscale Research Letters</i> , 2020, 15, 202.	5.7	25
22	A novel Ge based overlapping gate dopingless tunnel FET with high performance. <i>Japanese Journal of Applied Physics</i> , 2019, 58, 100902.	1.5	9
23	Probing the Field-Effect Transistor with Monolayer MoS ₂ Prepared by APCVD. <i>Nanomaterials</i> , 2019, 9, 1209.	4.1	10
24	A Horizontal-Gate Monolayer MoS ₂ Transistor Based on Image Force Barrier Reduction. <i>Nanomaterials</i> , 2019, 9, 1245.	4.1	10
25	Design and Investigation of a Dual Material Gate Arsenic Alloy Heterostructure Junctionless TFET with a Lightly Doped Source. <i>Applied Sciences (Switzerland)</i> , 2019, 9, 4104.	2.5	8
26	Design and Investigation of the High Performance Doping-Less TFET with Ge/Si _{0.6} Ge _{0.4} /Si Heterojunction. <i>Micromachines</i> , 2019, 10, 424.	2.9	10
27	A Doping-Less Tunnel Field-Effect Transistor with Si _{0.6} Ge _{0.4} Heterojunction for the Improvement of the On-Off Current Ratio and Analog/RF Performance. <i>Electronics (Switzerland)</i> , 2019, 8, 574.	3.1	9
28	Probing the Optical Properties of MoS ₂ on SiO ₂ /Si and Sapphire Substrates. <i>Nanomaterials</i> , 2019, 9, 740.	4.1	25
29	Design and Investigation of the Junction-Less TFET with Ge/Si _{0.3} Ge _{0.7} /Si Heterojunction and Heterogeneous Gate Dielectric. <i>Electronics (Switzerland)</i> , 2019, 8, 476.	3.1	14
30	Probing the Growth Improvement of Large-Size High Quality Monolayer MoS ₂ by APCVD. <i>Nanomaterials</i> , 2019, 9, 433.	4.1	9
31	Design and investigation of dopingless dual-gate tunneling transistor based on line tunneling. <i>AIP Advances</i> , 2019, 9, .	1.3	10
32	A New Electro-Optical Switch Modulator Based on the Surface Plasmon Polaritons of Graphene in Mid-Infrared Band. <i>Sensors</i> , 2019, 19, 89.	3.8	10
33	Research on the Factors Affecting the Growth of Large-Size Monolayer MoS ₂ by APCVD. <i>Materials</i> , 2018, 11, 2562.	2.9	6